

TENTATIVE

MITSUBISHI
ELECTRONIC DEVICE GROUP

OPTOELECTRONICS
HSO1

High Frequency Superimposition Module

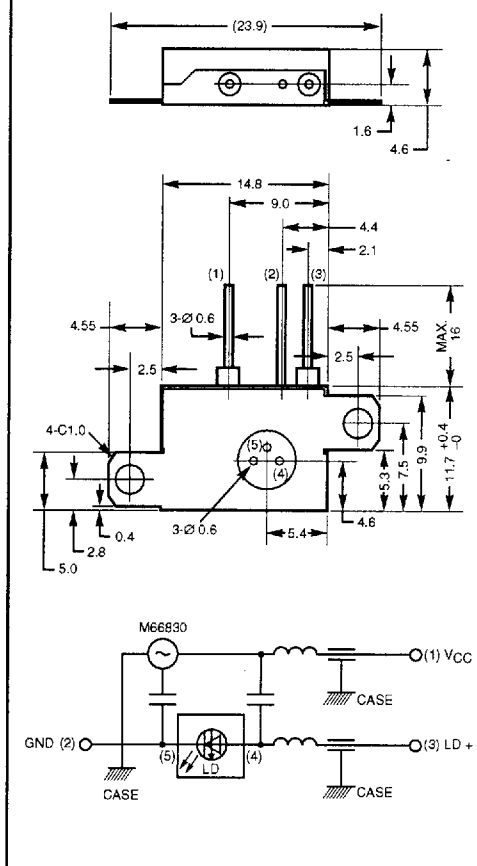
FEATURES

- Low noise RIN -125 dB/Hz Typ.
- Packing in shield case
- 5V single voltage supply

APPLICATION

- Optical disk memory
- Optical memory card

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Ratings	Unit
P _O	Light output power	35 (CW)	mW
		45 (pulse)	mW
V _{RL}	Reverse voltage (laser diode)	2	V
V _{RD}	Reverse voltage (photo diode)	30	V
T _c	Operating case temperature	-10 ~ +60	°C
T _{stg}	Storage temperature	-55 ~ +100	°C
V _{CC}	HF drive voltage	0 ~ +10	V

Optoelectronics



ELECTRICAL/OPTICAL CHARACTERISTICS (HF supply circuit) (T_c = 25°C)

Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{CC}	Supply voltage	—	4.5	5.0	5.5	V
I _{CC}	Supply current	—	—	—	100	mA
f _{osc}	Oscillation frequency	V _{CC} = 5V	200	300	400	MHz
t _r	Enable time	V _{CC} = 5V	—	—	1	μs

NOISE SPECIFICATION OF LASER DIODE (HF superimpose)

Parameter	Conditions	Limits			Unit
		Min.	Typ.	Max.	
R. I. N.	P _O = 3mW (average opt. power)	—	-125	—	dB/Hz

ML60111R 91-818099

R. I. N. vs. L_{ex}

HF Superposed by HSO1

